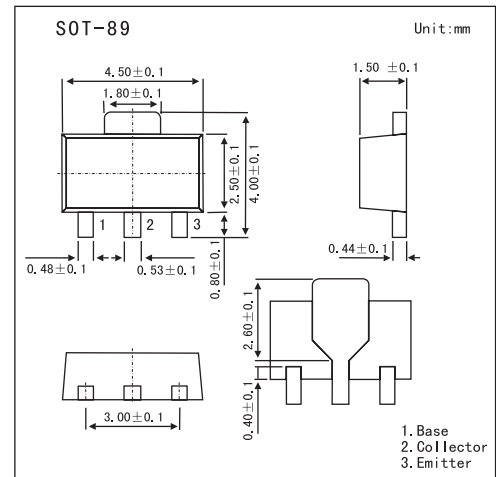


## Silicon PNP Epitaxial Planar Type

## 2SB1440

## ■ Features

- Low collector to emitter saturation voltage  $V_{CE(sat)}$ .
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-50	V
Collector-emitter voltage	$V_{CEO}$	-50	V
Emitter-base voltage	$V_{EBO}$	-5	V
Peak collector current	$I_{CP}$	-3	A
Collector current	$I_C$	-2	A
Collector power dissipation	$P_C$	1	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	$V_{CBO}$	$I_C = -10 \mu\text{A}$ , $I_E = 0$	-50			V
Collector-emitter voltage	$V_{CEO}$	$I_C = -1 \text{ mA}$ , $I_B = 0$	-50			V
Emitter-base voltage	$V_{EBO}$	$I_E = -10 \mu\text{A}$ , $I_C = 0$	-5			V
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -2 \text{ V}$ , $I_C = -200 \text{ mA}$	120		340	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1 \text{ A}$ , $I_B = -50 \text{ mA}$		-0.2	-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1 \text{ A}$ , $I_B = -50 \text{ mA}$		-0.85	-1.2	
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}$ , $I_E = 50 \text{ mA}$ , $f = 200 \text{ MHz}$		80		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10 \text{ V}$ , $I_E = 0$ , $f = 1 \text{ MHz}$		45	60	pF

## ■ hFE Classification

Marking	1I	
Rank	R	S
hFE	120~240	170~340